

## P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 20	0.150 at V <sub>GS</sub> = - 4.5 V	1.06	6.0
	0.166 at V <sub>GS</sub> = - 2.5V	1.0	
	0.214 at V <sub>GS</sub> = - 1.8V	0.49	

### FEATURES

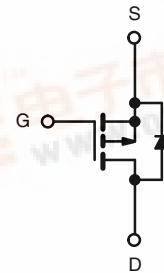
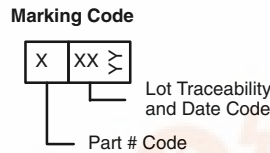
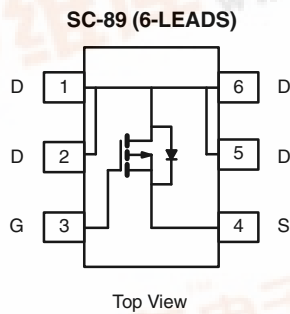
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Load Switch for Portable Devices



Ordering Information: Si1067X-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 20	V	
Gate-Source Voltage	V <sub>GS</sub>	± 8		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- 1.06 <sup>b, c</sup>	A	
	T <sub>A</sub> = 70 °C	- 0.85 <sup>b, c</sup>		
Pulsed Drain Current	I <sub>DM</sub>	- 8		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	- 0.2 <sup>b, c</sup>		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	0.236 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C	0.151 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a, b</sup>	t ≤ 5 s	440	530	°C/W	
	Steady State	540	650		

Notes:

- Maximum under steady state conditions is 650 °C/W.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.

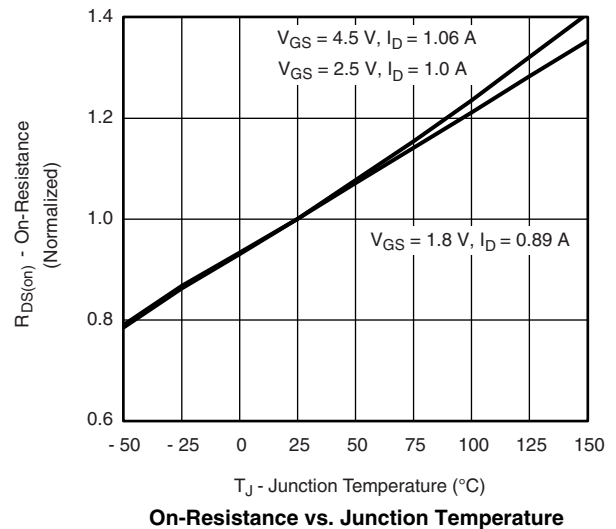
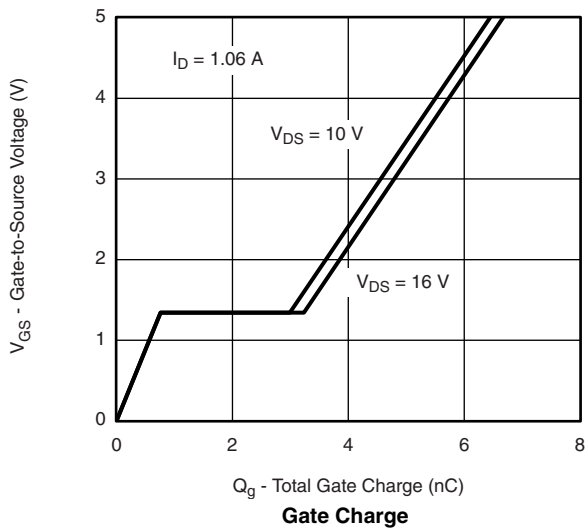
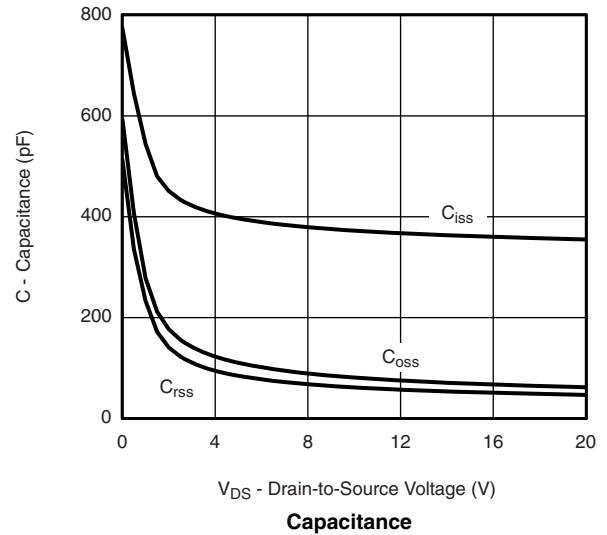
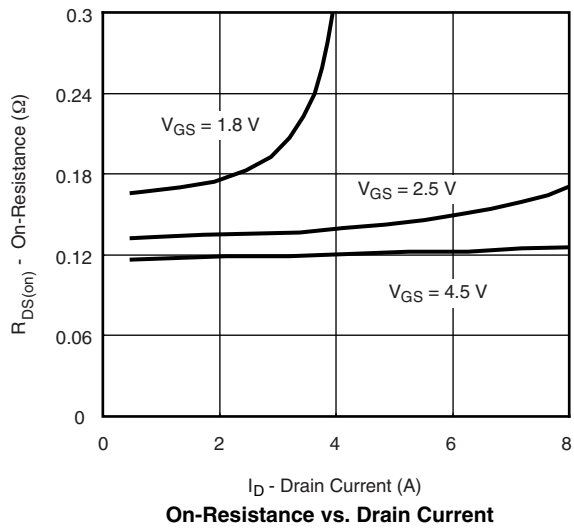
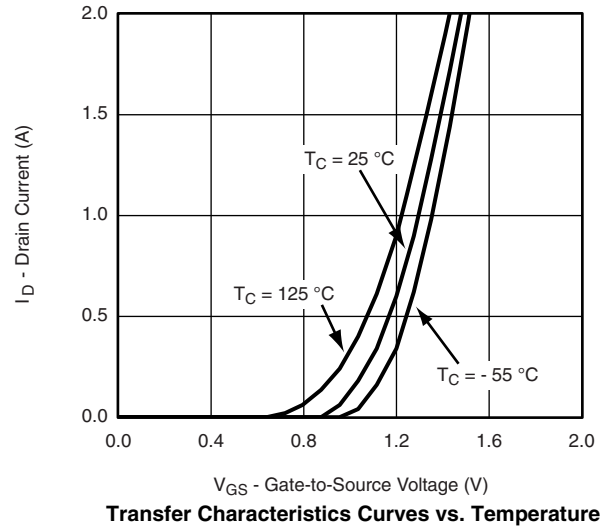
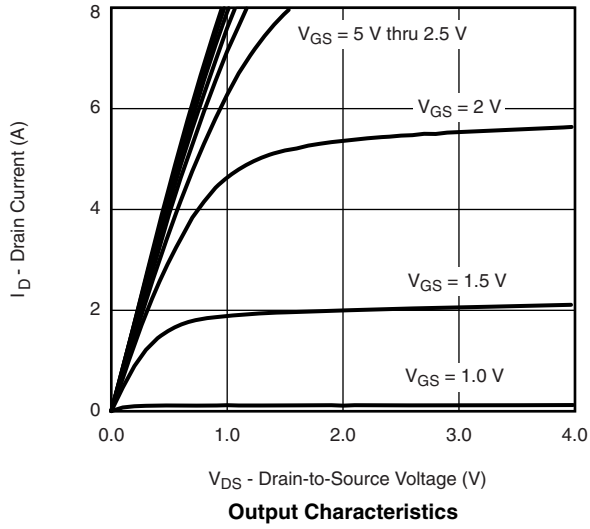
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-32.07		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			3.02		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.45		-0.95	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = \geq 5\text{ V}, V_{GS} = -4.5\text{ V}$	-8			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.06\text{ A}$		0.125	0.150	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -1.0\text{ A}$		0.138	0.166	
		$V_{GS} = -1.8\text{ V}, I_D = -0.49\text{ A}$		0.165	0.214	
Forward Transconductance	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -1.06\text{ A}$		4.0		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		375		pF
Output Capacitance	$C_{oss}$			82		
Reverse Transfer Capacitance	$C_{rss}$			62		
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -5\text{ V}, I_D = -1.06\text{ A}$		6.5	9.3	nC
			$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.06\text{ A}$		6.0	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.06\text{ A}$		0.76		nC
Gate-Drain Charge	$Q_{gd}$			2.23		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		8.8	13.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 19.74\text{ }\Omega$ $I_D \cong -0.76\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		14	21	ns
Rise Time	$t_r$			22	33	
Turn-Off Delay Time	$t_{d(off)}$			48	72	
Fall Time	$t_f$			17	25.5	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				8	A
Body Diode Voltage	$V_{SD}$	$I_S = -0.63\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -0.7\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		12.8	19.2	nC
Body Diode Reverse Recovery Charge	$Q_{rr}$			4.5	6.8	ns
Reverse Recovery Fall Time	$t_a$			7.3		
Reverse Recovery Rise Time	$t_b$			5.5		

## Notes:

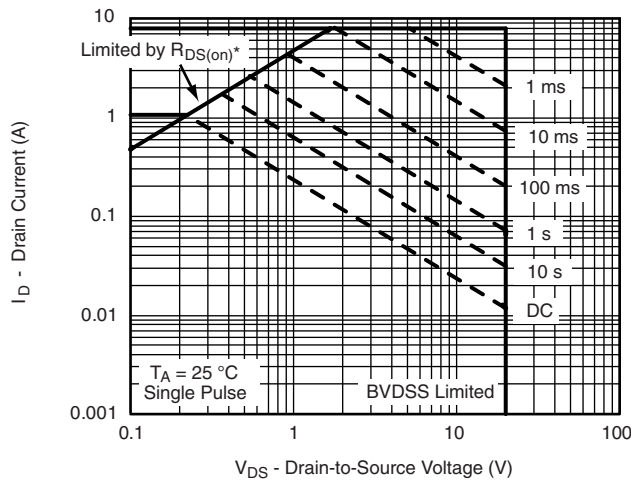
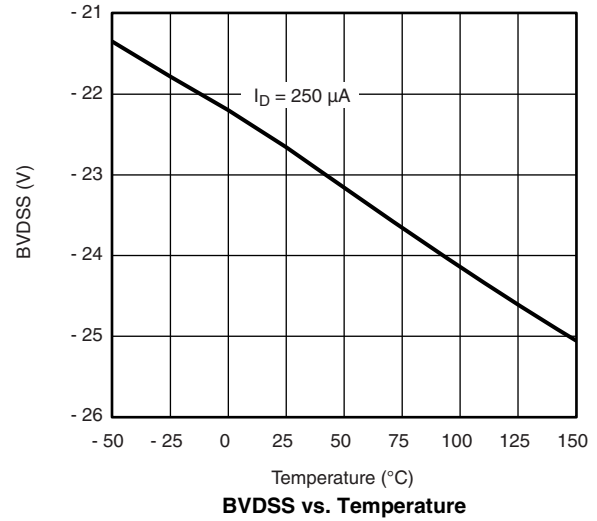
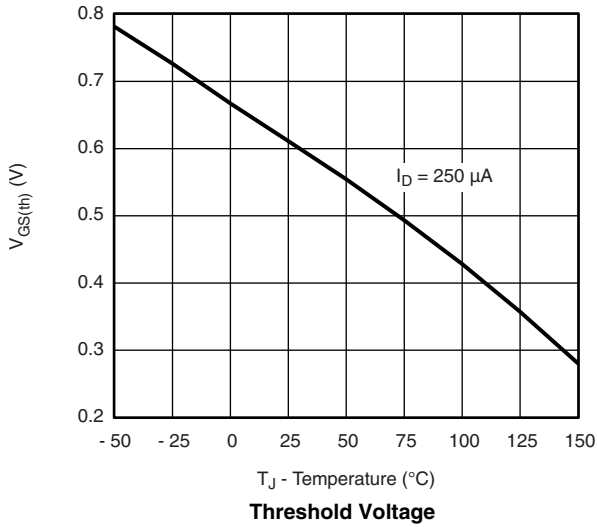
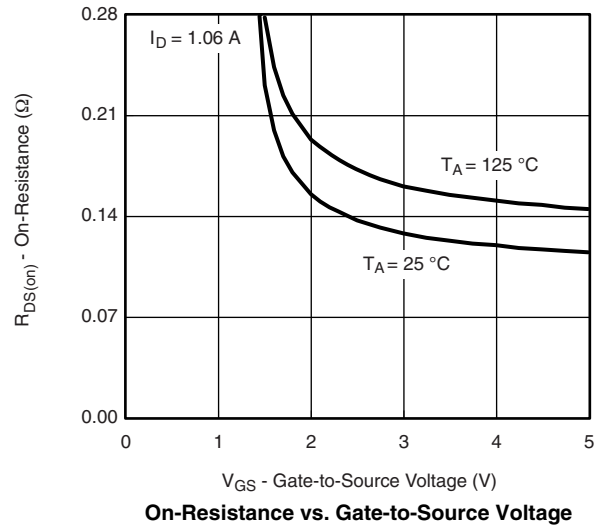
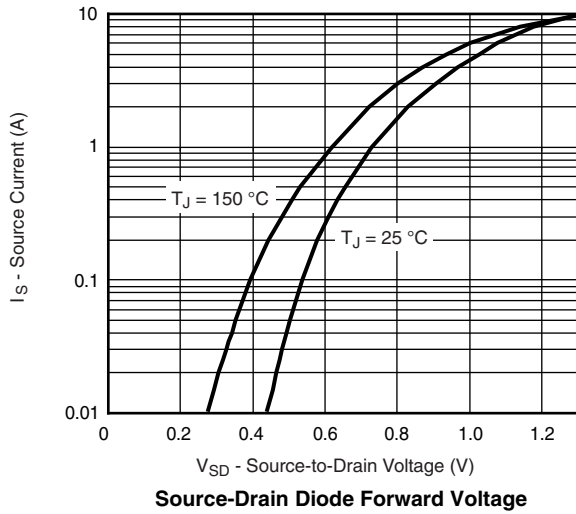
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

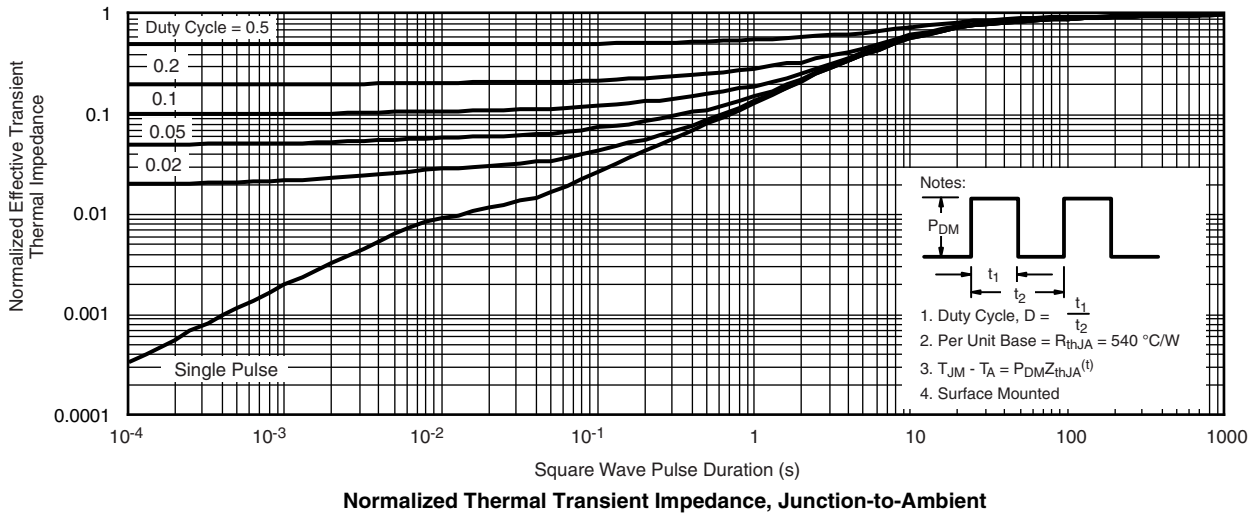


## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified  
**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



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